

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
30	0.022 at V _{GS} = 10 V	7.5
	0.030 at V _{GS} = 4.5 V	6.5

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 at 1 A	2.0

FEATURES

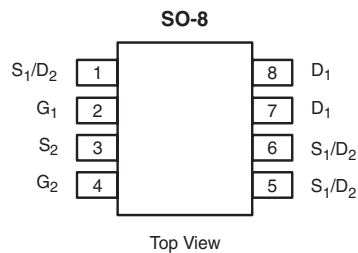
- LITTLE FOOT® Plus Schottky
- Si4830DY Pin Compatible
- PWM Optimized
- 100 % R_g Tested



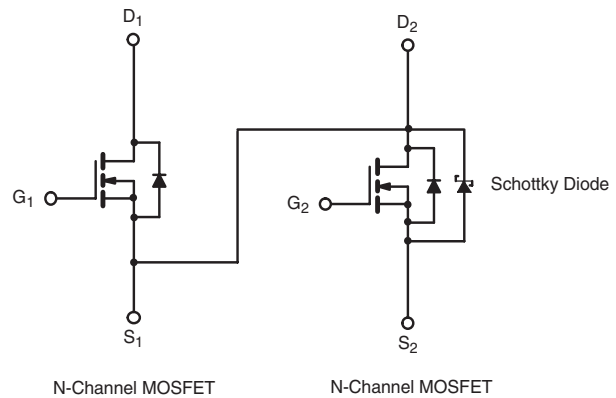
RoHS
COMPLIANT

APPLICATIONS

- Asymmetrical Buck-Boost DC/DC Converter



Ordering Information: Si4830ADY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	30		V
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	7.5	5.7
		T _A = 70 °C	6.0	4.6
Pulsed Drain Current	I _{DM}	30		A
Continuous Source Current (Diode Conduction) ^a	I _S	1.7	0.9	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.0	1.1
		T _A = 70 °C	1.3	0.7
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	MOSFET		SCHOTTKY		Unit
		Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	52	62.5	53	62.5
		Steady State	93	110	93	110
Maximum Junction-to-Foot (Drain)	R _{thJF}	35	40	35	40	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.4		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$	Ch-1		1	μA
			Ch-2		100	
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 85\text{ }^\circ\text{C}$	Ch-1		15	
			Ch-2		2000	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}$, $V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 7.5\text{ A}$		0.017	0.022	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = -6.5\text{ A}$		0.024	0.030	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 7.5\text{ A}$		19		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$	Ch-1	0.75	1.2	V
			Ch-2	0.47	0.5	
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 7.5\text{ A}$		7	11	nC
Gate-Source Charge	Q_{gs}			2.9		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g		0.5	1.5	2.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		9	15	ns
Rise Time	t_r			10	17	
Turn-Off Delay Time	$t_{d(off)}$			19	30	
Fall Time	t_f			9	15	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 1.7\text{ A}$, $di/dt = 100\text{ }\mu\text{s}$	Ch-1	35	
		Ch-2		32	55	

Notes:

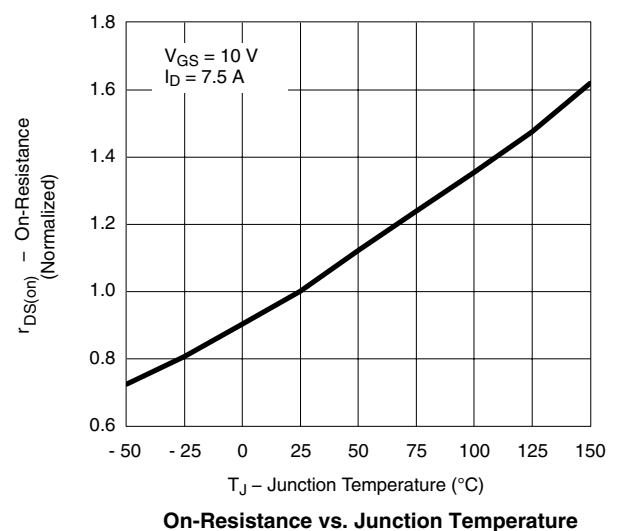
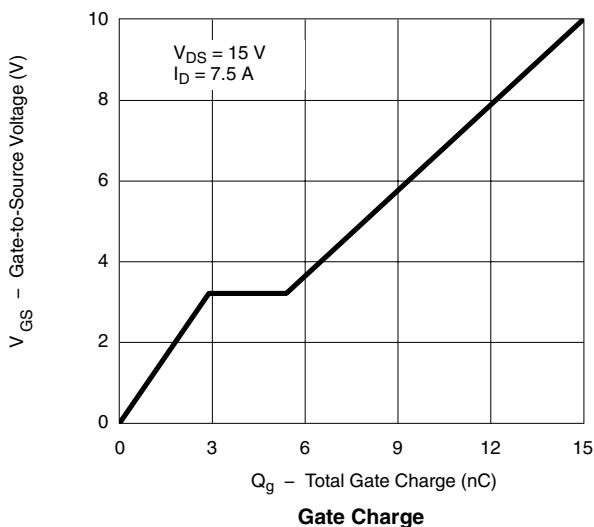
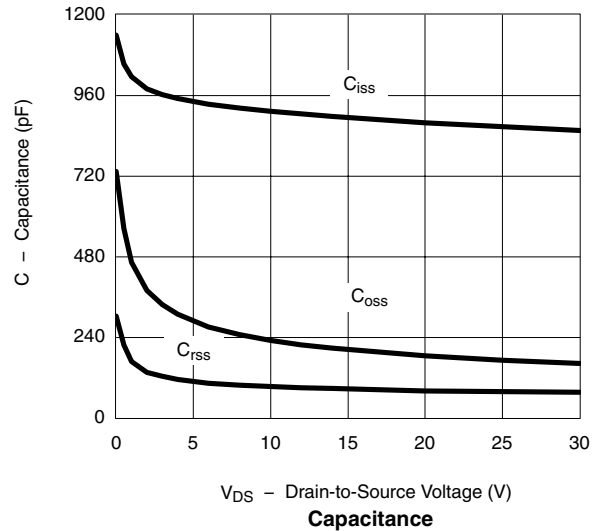
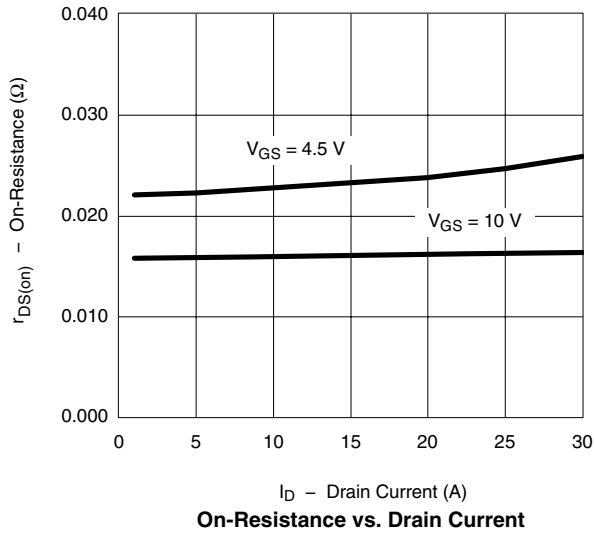
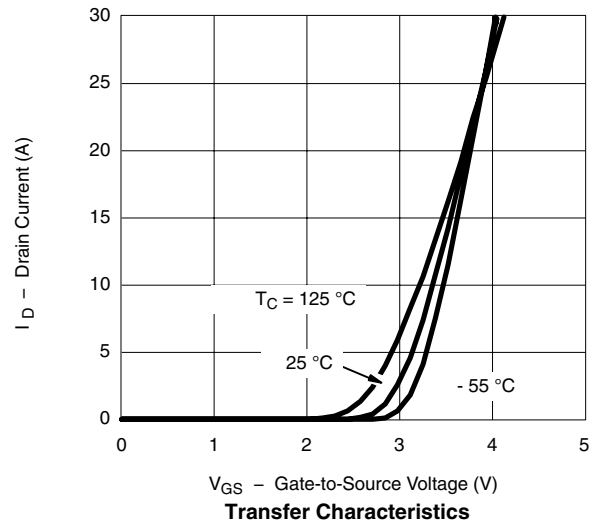
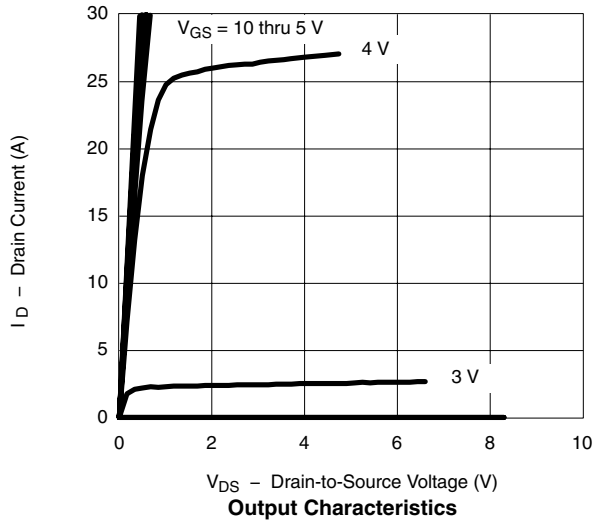
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

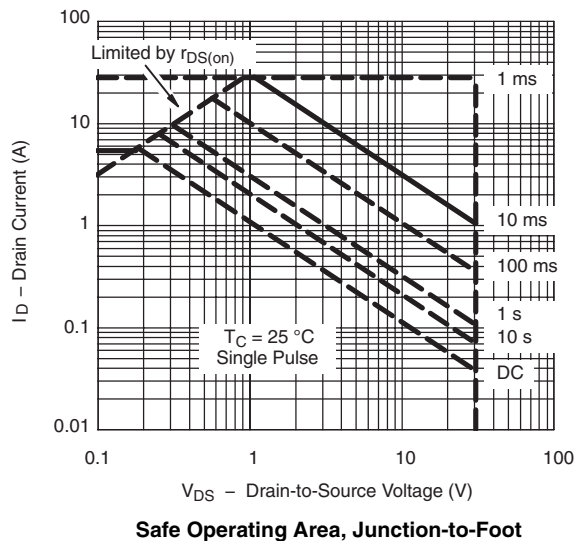
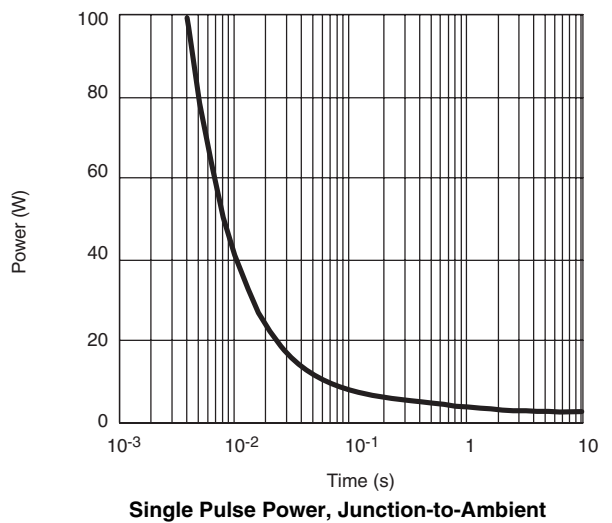
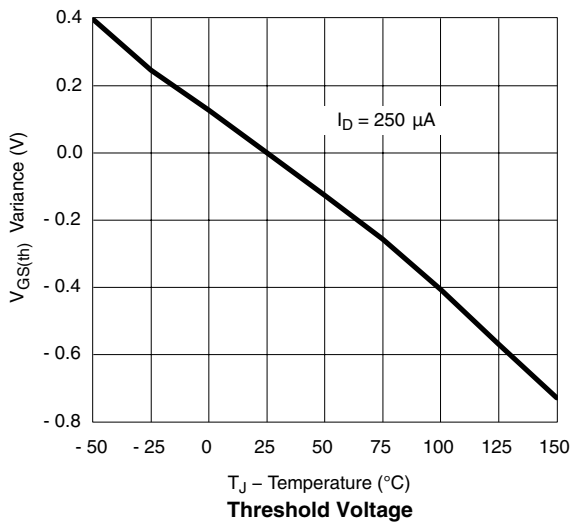
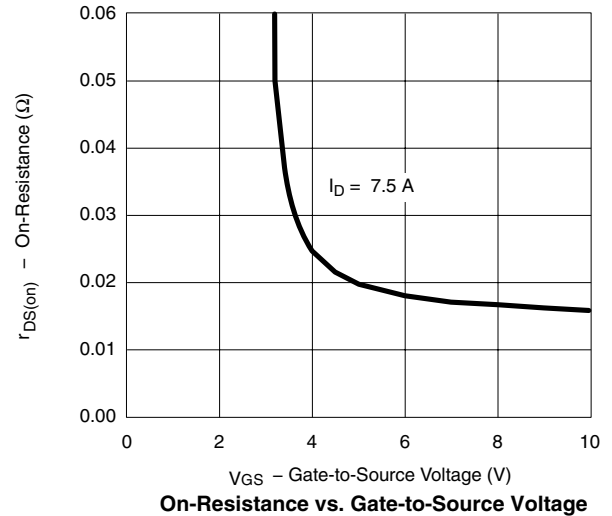
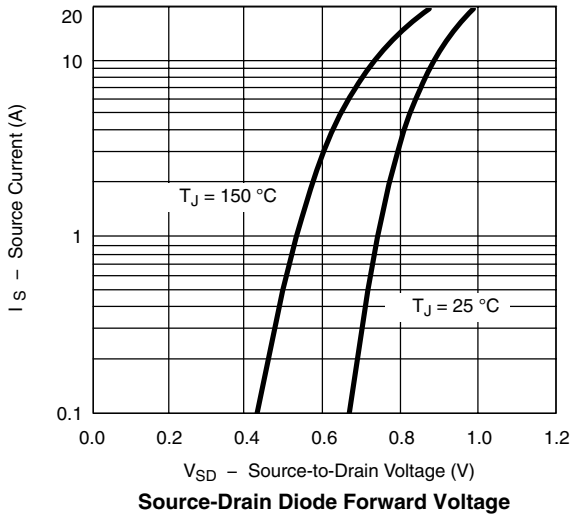
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30\text{ V}$		0.004	0.100	mA
		$V_r = 30\text{ V}$, $T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_r = -30\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_r = 10\text{ V}$		50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

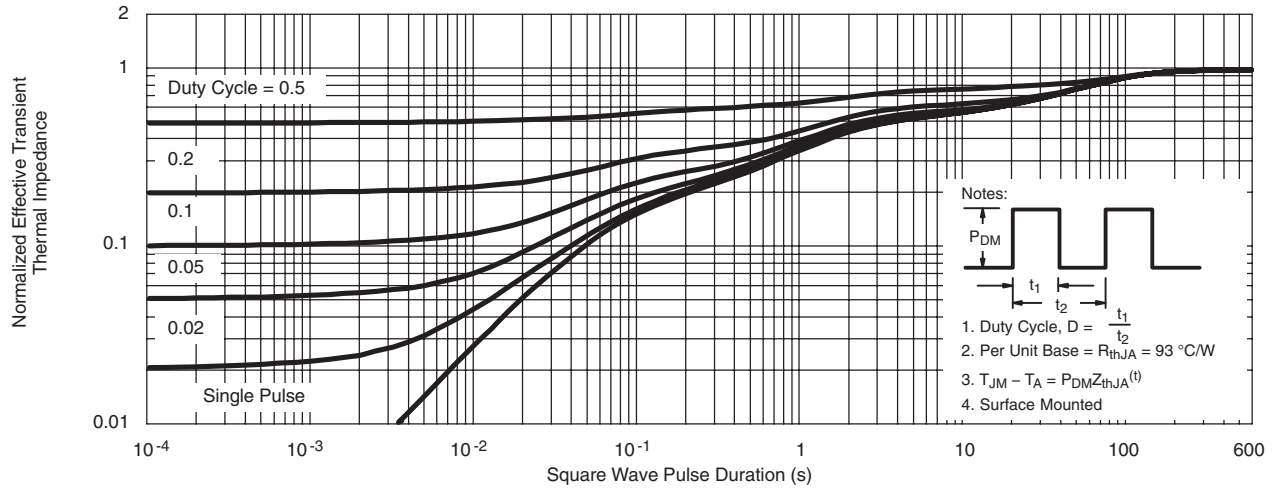
MOSFET TYPICAL CHARACTERISTICS 25 °C unless noted



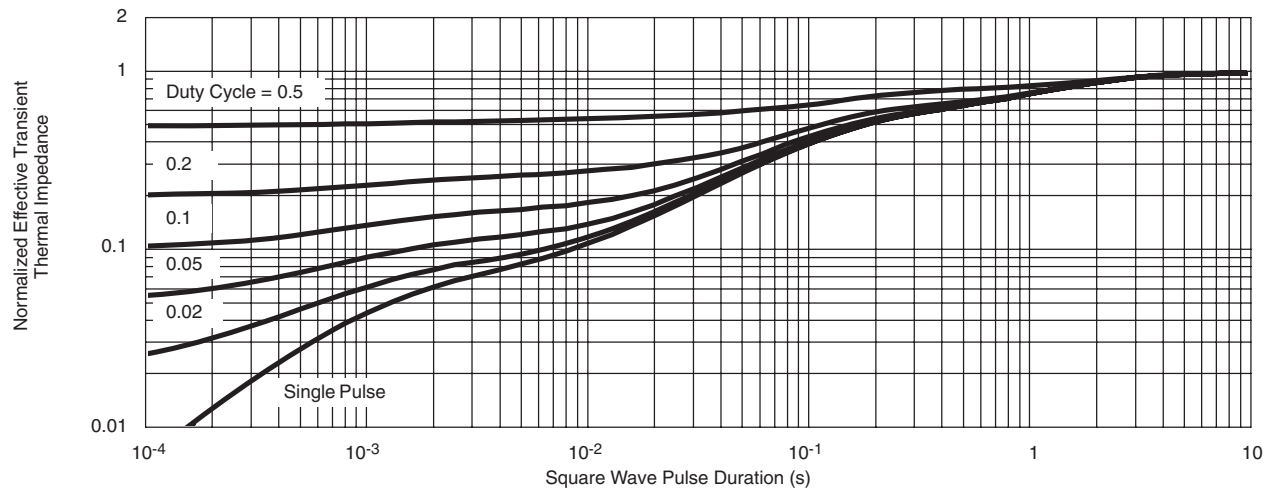
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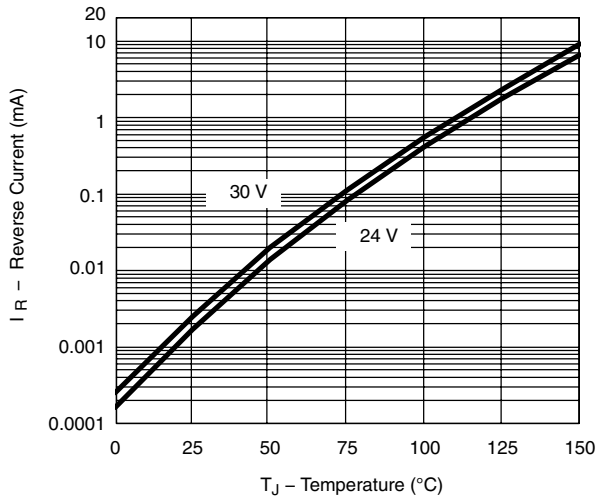


Normalized Thermal Transient Impedance, Junction-to-Ambient

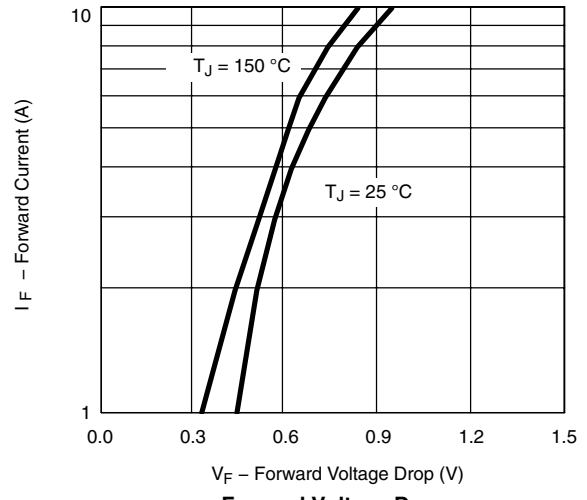


Normalized Thermal Transient Impedance, Junction-to-Foot

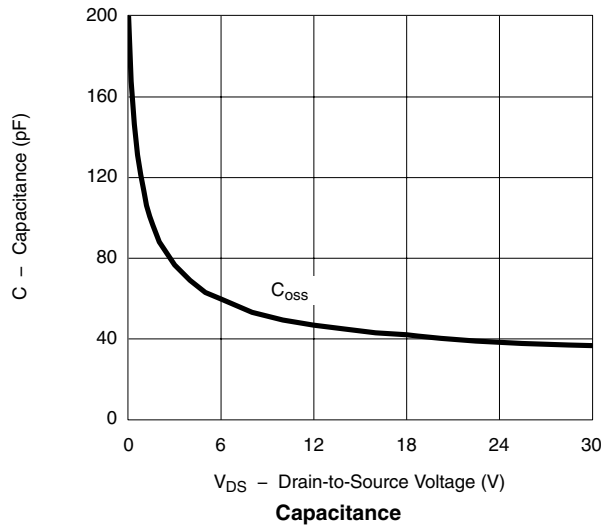
MOSFET TYPICAL CHARACTERISTICS 25 °C unless noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop



Capacitance

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